Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

1. (Currently Amended) A semiconductor device comprising:

a semiconductor layer over an insulating surface;

a gate insulating film on said semiconductor layer; ~~and~~

a gate electrode on said gate insulating film~~,~~; and

an interlayer insulating film on said gate electrode,

wherein said semiconductor layer comprises a channel formation region, at least one LDD region in contact with said channel formation region, and a source region or a drain region in contact with said LDD region,

wherein said gate electrode has a taper shape, ~~and~~

wherein said gate electrode comprises a laminate of a fourth electrode, a fifth electrode on said fourth electrode and a sixth electrode on said fifth electrode, ~~and at least one of~~ the fourth electrode comprises tungsten, the fifth electrode comprises copper as its main component and the sixth electrode comprises ~~copper~~ titanium, and

wherein said interlayer insulating film contacts said fifth electrode.

2. (Currently Amended) A semiconductor device comprising:

a semiconductor layer over an insulating surface;

a gate insulating film on said semiconductor layer; ~~and~~

a gate electrode on said gate insulating film~~,~~; and

an interlayer insulating film on said gate electrode,

wherein said semiconductor layer comprises a channel formation region, at least one LDD region in contact with said channel formation region, and one of a source region and a drain region in contact with said LDD region,

wherein said LDD region comprises a impurity region for giving one conductivity at a concentration of 1×10^{17} to 1×10^{20} atoms/cm^3, and one of said source region and said drain region comprises said impurity element at a concentration of 1×10^{20} to 1×10^{21} atoms /cm^3,

wherein said gate electrode has a taper shape, and

wherein said gate electrode comprises a laminate of a fourth electrode, a fifth electrode on said fourth electrode and a sixth electrode on said fifth electrode, ~~and at least one of~~ the fourth electrode comprises tungsten, the fifth electrode comprises copper as its main component and the sixth electrode comprises ~~copper~~ titanium, and

wherein said interlayer insulating film contacts said fifth electrode.

3-4. (Canceled)

5. (Original) The semiconductor device as claimed in claim 1, said fourth electrode is overlapped with said LDD region through said gate insulating film.

6. (Original) The semiconductor device as claimed in claim 2, said fourth electrode is overlapped with said LDD region through said gate insulating film.

7-24. (Canceled)

25. (Original) The semiconductor device as claimed in claim 1, wherein said semiconductor device is selected from the group consisting of a computer, a video camera, a digital camera, a mobile telephone, and a projector.

26. (Original) The semiconductor device as claimed in claim 2, wherein said semiconductor device is selected from the group consisting of a computer, a video camera, a digital camera, a mobile telephone, and a projector.

27. (Withdrawn) A semiconductor device comprising:

a semiconductor layer over an insulating surface;

a gate insulating film on said semiconductor layer; and

a gate electrode on said gate insulating film,

wherein said semiconductor layer comprises a channel formation region, at least one LDD region in contact with said channel formation region, and a source region or a drain region in contact with said LDD region,

wherein said gate electrode has a taper shape,

wherein said gate electrode comprises a laminate of a fourth electrode, a fifth electrode and a sixth electrode, and at least one of the fourth electrode, the fifth electrode and the sixth electrode comprises copper, and

wherein the semiconductor device has an external input terminal portion with a first portion covered by a conductive film comprising the fourth electrode, the fifth electrode or the sixth electrode and a second portion covered by the gate insulating film and an interlayer insulating film arranged alternately.

28. (Withdrawn) A semiconductor device comprising:

a semiconductor layer over an insulating surface;

a gate insulating film on said semiconductor layer; and

a gate electrode on said gate insulating film,

wherein said semiconductor layer comprises a channel formation region, at least one LDD region in contact with said channel formation region, and one of a source region and a drain region in contact with said LDD region,

wherein said LDD region comprises an impurity region for giving one conductivity at a concentration of 1×10^{17} to 1×10^{20} atoms/cm^3, and one of said source region and said drain region comprises said impurity element at a concentration of 1×10^{20} to 1×10^{21} atoms /cm^3,

wherein said gate electrode has a taper shape,

wherein said gate electrode comprises a laminate of a fourth electrode, a fifth electrode and a sixth electrode, and at least one of the fourth electrode, the fifth electrode and the sixth electrode comprises copper, and

wherein the semiconductor device has an external input terminal portion with a first portion covered by a conductive film comprising the fourth electrode, the fifth electrode or the sixth electrode and a second portion covered by the gate insulating film and an interlayer insulating film arranged alternately.

29-30. (Canceled).

31. (Withdrawn) The semiconductor device as claimed in claim 27, wherein said fourth electrode is formed of a conductive film comprising tungsten or a material including tungsten as its main component, said fifth electrode is formed of a conductive film comprising copper or a material including copper as its main component, and said sixth electrode is formed of a conductive film comprising titanium or a material including titanium as its main component.

32. (Withdrawn) The semiconductor device as claimed in claim 28, wherein said fourth electrode is formed of a conductive film comprising tungsten or a material including tungsten as its main component, said fifth electrode is formed of a conductive film comprising copper or a material including copper as its main component, and said sixth electrode is formed of a conductive film comprising titanium or a material including titanium as its main component.

33. (Withdrawn) The semiconductor device as claimed in claim 27, wherein said fourth electrode is overlapped with said LDD region through said gate insulating film.

34. (Withdrawn) The semiconductor device as claimed in claim 28, wherein said fourth electrode is overlapped with said LDD region through said gate insulating film.

35. (Withdrawn) The semiconductor device as claimed in claim 27, wherein said semiconductor device is selected from the group consisting of a computer, a video camera, a digital camera, a mobile telephone, and a projector.

36. (Withdrawn) The semiconductor device as claimed in claim 28, wherein said semiconductor device is selected from the group consisting of a computer, a video camera, a digital camera, a mobile telephone, and a projector.

37. (New) A semiconductor device comprising:

a semiconductor layer over an insulating surface;

a gate insulating film on said semiconductor layer;

a gate electrode on said gate insulating film; and

an interlayer insulating film on said gate electrode,

wherein said semiconductor layer comprises a channel formation region, at least one LDD region in contact with said channel formation region, and a source region or a drain region in contact with said LDD region,

wherein said gate electrode has a taper shape,

wherein said gate electrode comprises a laminate of a fourth electrode, a fifth electrode on said fourth electrode and a sixth electrode on said fifth electrode, the fourth electrode comprises one of tungsten, molybdenum and tantalum as its main component, the fifth electrode comprises copper as its main component and the sixth electrode comprises titanium, and

wherein said interlayer insulating film contacts said fifth electrode.

38. (New) A semiconductor device comprising:

a semiconductor layer over an insulating surface;

a gate insulating film on said semiconductor layer;

a gate electrode on said gate insulating film; and

an interlayer insulating film on said gate electrode,

wherein said semiconductor layer comprises a channel formation region, at least one LDD region in contact with said channel formation region, and one of a source region and a drain region in contact with said LDD region,

wherein said LDD region comprises a impurity region for giving one conductivity at a concentration of 1×10^{17} to 1×10^{20} atoms/cm^3, and one of said source region and said drain region comprises said impurity element at a concentration of 1×10^{20} to 1×10^{21} atoms /cm^3,

wherein said gate electrode has a taper shape, and

wherein said gate electrode comprises a laminate of a fourth electrode, a fifth electrode on said fourth electrode and a sixth electrode on said fifth electrode, the fourth electrode comprises one of tungsten, molybdenum and tantalum as its main component, the fifth electrode comprises copper as its main component and the sixth electrode comprises titanium, and

wherein said interlayer insulating film contacts said fifth electrode.

39. (New) The semiconductor device as claimed in claim 37, said fourth electrode is overlapped with said LDD region through said gate insulating film.

40. (New) The semiconductor device as claimed in claim 38, said fourth electrode is overlapped with said LDD region through said gate insulating film.

41. (New) The semiconductor device as claimed in claim 37, wherein said semiconductor device is selected from the group consisting of a computer, a video camera, a digital camera, a mobile telephone, and a projector.

42. (New) The semiconductor device as claimed in claim 38, wherein said semiconductor device is selected from the group consisting of a computer, a video camera, a digital camera, a mobile telephone, and a projector.